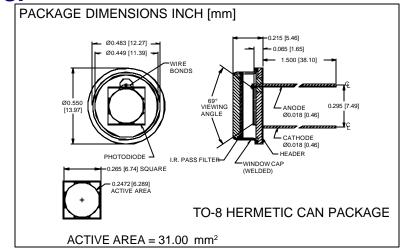
## **PHOTONIC** DETECTORS INC.

### Silicon Photodiode, Near I.R. Photoconductive Type PDI-C108-F





#### **FEATURES**

- High speed
- Match to I.R. emitters
- Hermetic package

### **DESCRIPTION**

The PDI-C108-F is a silicon, PIN planar • I.R. pass visible rejection diffused photodiode with NIR pass, visible light rejection optical filter. Ideal for high speed, low capacitance, photoconductive NIR applications. Packaged in a hermetic

# TO-8 metal can with a flat window cap. ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

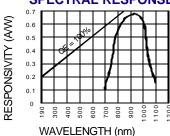
SYMBOL	PARAMETER	MIN	MAX	UNITS
V <sub>BR</sub>	Reverse Voltage		100	V
T <sub>stg</sub>	Storage Temperature	-55	+100	°C
То	Operating Temperature Range	-40	+80	°C
Ts	Soldering Temperature*		+240	°C
I <sub>L</sub>	Light Current		1.0	mA

\*1/16 inch from case for 3 secs max

### **APPLICATIONS**

- I.R. detector
- I.R. laser detector
- Photo-interrupters
- Industrial controls

### **SPECTRAL RESPONSE**



### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

2220110 Of 110/12 Off/11/10/100 (1/1-20 off/11/10/100)									
SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS			
lsc	Short Circuit Current	H = 100 fc, 2850 K	360	414		mA			
ΙD	Dark Current	$H = 0, V_R = 10 V$		5	15	nA			
RsH	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$	65	120		MΩ			
TC Rsh	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-8		%/℃			
Cı	Junction Capacitance	$H = 0$ , $V_R = 10 V^{**}$		75		pF			
λrange	Spectral Application Range	Spot Scan	700		1100	nm			
λр	Spectral Response - Peak	Spot Scan		950		nm			
V <sub>BR</sub>	Breakdown Voltage	I = 10 <b>m</b> A	100	125		V			
N EP	Noise Equivalent Power	VR = 10 V @ Peak		8x10 <sup>-13</sup>		W/ √Hz			
tr	Response Time	$RL = 1 K\Omega V_p = 50 V$		20		nS			

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. \*\* f = 1 MHz